## NSN 5961-00-277-7386

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Inclosure Material:
Metal all transistor
Overall Length:
0.170 inches all transistor and 0.210 inches all transistor
Terminal Length:
0.500 inches all transistor
Overall Diameter:
0.209 inches all transistor and 0.230 inches all transistor
Internal Configuration:
Junction contact all transistor
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-18 all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
2 transistor
Mounting Method:
Terminal all transistor
Terminal Circle Diameter:
0.100 inches all transistor
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
12.0 breakdown voltage, collector-to-emitter, base open all transistor
Power Rating Per Characteristic:
400.0 watts small-signal input power, common-collector absolute all transistor
Transfer Ratio:
40.0 static forward current transfer ratio, common-emitter all transistor and 200.0 static forward current transfer ratio, common-emitter all
transistor
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction all transistor
Terminal Type And Quantity:
3 uninsulated wire lead all transistor
Shelf Life:
N/a
Unit Of Measure:

No

Demilitarization:

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